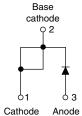
### VS-MUR820PbF, VS-MUR820-N3

Vishay Semiconductors

# Ultrafast Rectifier, 8 A FRED Pt®

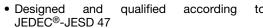




TO-220AC

## FEATURES

- Ultrafast recovery time
- Low forward voltage drop
- 175 °C operating junction temperature
- Low leakage current



 Material categorization: for definitions of compliance please see <a href="https://www.vishav.com/doc?99912"><u>www.vishav.com/doc?99912</u></a>



#### **DESCRIPTION / APPLICATIONS**

VS-MUR820PbF is the state of the art ultrafast recovery rectifier specifically designed with optimized performance of forward voltage drop and ultrafast recovery time.

The planar structure and the platinum doped life time control, guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in the output rectification stage of SMPS, UPS, DC/DC converters as well as freewheeling diode in low voltage inverters and chopper motor drives.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

PRODUCT SUMMARY	
Package	TO-220AC
I <sub>F(AV)</sub>	8 A
$V_{R}$	200 V
V <sub>F</sub> at I <sub>F</sub>	0.895 V
t <sub>rr</sub> typ.	See Recovery table
T <sub>J</sub> max.	175 °C
Diode variation	Single die
	•

ABSOLUTE MAXIMUM RATINGS							
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS			
Peak repetitive reverse voltage	$V_{RRM}$		200	V			
Average rectified forward current	I <sub>F(AV)</sub>	Total device, rated V <sub>R</sub> , T <sub>C</sub> = 150 °C	8				
Non-repetitive peak surge current	I <sub>FSM</sub>		100	Α			
Peak repetitive forward current	I <sub>FM</sub>	Rated V <sub>R</sub> , square wave, 20 kHz, T <sub>C</sub> = 150 °C	16				
Operating junction and storage temperatures	T <sub>J</sub> , T <sub>Stg</sub>		-65 to +175	°C			

<b>ELECTRICAL SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Breakdown voltage, blocking voltage	V <sub>BR</sub> , V <sub>R</sub>	Ι <sub>R</sub> = 100 μΑ	200	-	-		
Forward voltage	V <sub>F</sub>	I <sub>F</sub> = 8 A	-	-	0.975	V	
		I <sub>F</sub> = 8 A, T <sub>J</sub> = 150 °C	-	-	0.895	r	
		V <sub>R</sub> = V <sub>R</sub> rated	-	-	5		
Reverse leakage current I <sub>R</sub>		T <sub>J</sub> = 150 °C, V <sub>R</sub> = V <sub>R</sub> rated	-	-	250	μΑ	
Junction capacitance	C <sub>T</sub>	V <sub>R</sub> = 200 V	-	25	-	pF	
Series inductance	L <sub>S</sub>	Measured lead to lead 5 mm from package body	-	8.0	-	nH	



# VS-MUR820PbF, VS-MUR820-N3

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<b>DYNAMIC RECOVERY CHARACTERISTICS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CO	MIN.	TYP.	MAX.	UNITS		
		$I_F = 1.0 \text{ A}, dI_F/dt =$	$50 \text{ A/}\mu\text{s}, V_{\text{R}} = 30 \text{ V}$	i	1	35		
Reverse recovery time	t <sub>rr</sub>	I <sub>F</sub> = 0.5 A, I <sub>R</sub> = 1.0 A, I <sub>REC</sub> = 0.25 A		-	-	25	no	
neverse recovery time		T <sub>J</sub> = 25 °C	I <sub>F</sub> = 8 A dI <sub>F</sub> /dt = 200 A/μs V <sub>R</sub> = 160 V	-	20	-	ns	
		T <sub>J</sub> = 125 °C		-	34	-		
Dook roopyon, ourrent	I <sub>RRM</sub>	T <sub>J</sub> = 25 °C		-	1.7	-	Α	
Peak recovery current		T <sub>J</sub> = 125 °C		-	4.2	-	^	
Reverse recovery charge	0	T <sub>J</sub> = 25 °C		=	23	-	0	
	Q <sub>rr</sub>	T <sub>J</sub> = 125 °C		-	75	-	nC	

THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Maximum junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-65	-	175	°C	
Thermal resistance, junction to case	R <sub>thJC</sub>		-	-	3.0		
Thermal resistance, junction to ambient	R <sub>thJA</sub>		-	-	50	°C/W	
Thermal resistance, case to heatsink	R <sub>thCS</sub>	Mounting surface, flat, smooth and greased	-	0.5	-		
Woight			-	2.0	-	g	
Weight			-	0.07	-	OZ.	
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)	
Marking device		Case style TO-220AC		MUF	R820		



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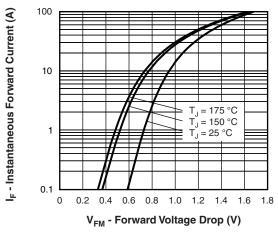


Fig. 1 - Maximum Forward Voltage Drop Characteristics

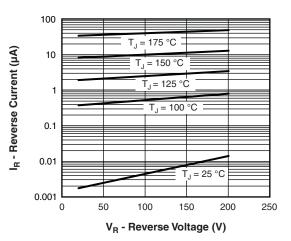


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

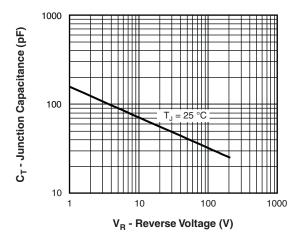


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

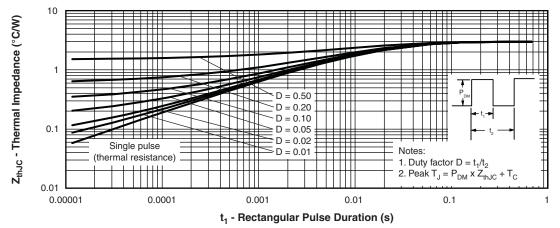


Fig. 4 - Maximum Thermal Impedance Z<sub>thJC</sub> Characteristics

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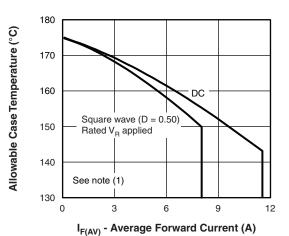


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current

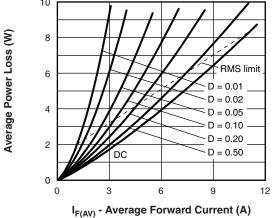
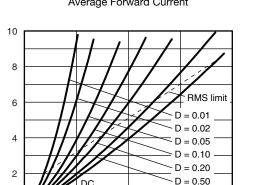


Fig. 6 - Forward Power Loss Characteristics



#### Note

<sup>(1)</sup> Formula used:  $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$ ; Pd = Forward power loss =  $I_{F(AV)} \times V_{FM}$  at  $(I_{F(AV)}/D)$  (see fig. 6); Pd<sub>REV</sub> = Inverse power loss =  $V_{R1} \times I_R$  (1 - D);  $I_R$  at  $V_{R1}$  = Rated  $V_R$ 

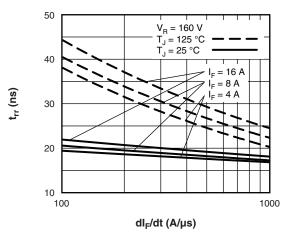


Fig. 7 - Typical Reverse Recovery Time vs. dl<sub>F</sub>/dt

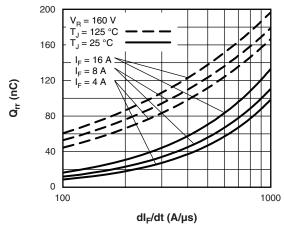


Fig. 8 - Typical Stored Charge vs. dl<sub>F</sub>/dt

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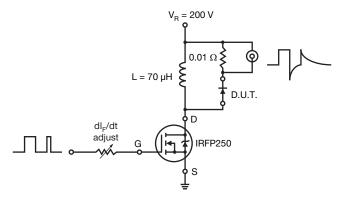
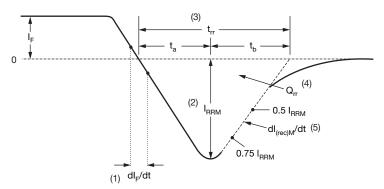


Fig. 9 - Reverse Recovery Parameter Test Circuit



- (1) dl<sub>F</sub>/dt rate of change of current through zero crossing
- (2) I<sub>RRM</sub> peak reverse recovery current
- (3)  $\rm t_{rr}$  reverse recovery time measured from zero crossing point of negative going  $\rm I_F$  to point where a line passing through 0.75  $\rm I_{RRM}$  and 0.50  $\rm I_{RRM}$  extrapolated to zero current.
- (4)  $\mathbf{Q}_{\rm rr}$  area under curve defined by  $\mathbf{t}_{\rm rr}$  and  $\mathbf{I}_{\rm RRM}$

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5)  $dI_{(rec)M}/dt$  - peak rate of change of current during  $t_b$  portion of  $t_{rr}$ 

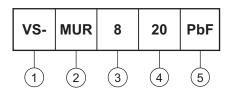
Fig. 10 - Reverse Recovery Waveform and Definitions

# VS-MUR820PbF, VS-MUR820-N3

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#### **ORDERING INFORMATION TABLE**

**Device code** 



1 - Vishay Semiconductors product

2 - Ultrafast MUR series

3 - Current rating (8 = 8 A)

Voltage rating (20 = 200 V)

5 - Environmental digit:

PbF = lead (Pb)-free and RoHS,compliant

-N3 = halogen-free, RoHS-compliant, and totally lead (Pb)-free

ORDERING INFORMATION (Example)						
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION			
VS-MUR820PbF	50	1000	Antistatic plastic tube			
VS-MUR820-N3	50	1000	Antistatic plastic tube			

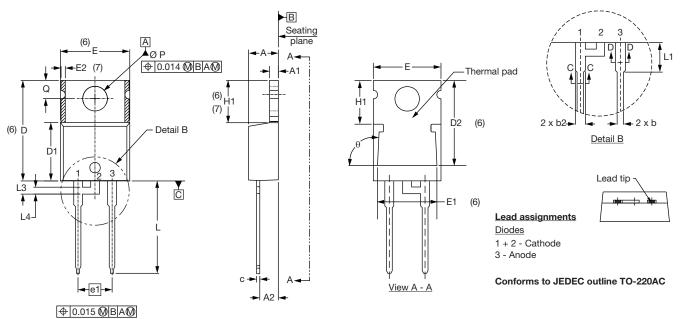
LINKS TO RELATED DOCUMENTS					
Dimensions <u>www.vishay.com/doc?95221</u>					
Dort marking information	TO-220ACPbF	www.vishay.com/doc?95224			
Part marking information	TO-220AC-N3	www.vishay.com/doc?95068			



### Vishay Semiconductors

#### **TO-220AC**

#### **DIMENSIONS** in millimeters and inches



SYMBOL	MILLIN	IETERS	INCHES		NOTES
STIVIBUL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.25	4.65	0.167	0.183	
A1	1.14	1.40	0.045	0.055	
A2	2.56	2.92	0.101	0.115	
b	0.69	1.01	0.027	0.040	
b1	0.38	0.97	0.015	0.038	4
b2	1.20	1.73	0.047	0.068	
b3	1.14	1.73	0.045	0.068	4
С	0.36	0.61	0.014	0.024	
c1	0.36	0.56	0.014	0.022	4
D	14.85	15.25	0.585	0.600	3
D1	8.38	9.02	0.330	0.355	
D2	11.68	12.88	0.460	0.507	6
Е	10.11	10.51	0.398	0.414	3, 6

SYMBOL	MILLIM	IETERS	INCHES		NOTES
STINIBUL	MIN.	MAX.	MIN.	MAX.	NOTES
E1	6.86	8.89	0.270	0.350	6
E2	-	0.76	-	0.030	7
е	2.41	2.67	0.095	0.105	
e1	4.88	5.28	0.192	0.208	
H1	6.09	6.48	0.240	0.255	6, 7
L	13.52	14.02	0.532	0.552	
L1	3.32	3.82	0.131	0.150	2
L3	1.78	2.13	0.070	0.084	
L4	0.76	1.27	0.030	0.050	2
ØΡ	3.54	3.73	0.139	0.147	
Q	2.60	3.00	0.102	0.118	
θ	90° t	o 93°	90° to 93°		

#### Notes

- (1) Dimensioning and tolerancing as per ASME Y14.5M-1994
- (2) Lead dimension and finish uncontrolled in L1
- (3) Dimension D, D1 and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Dimension b1, b3 and c1 apply to base metal only
- (5) Controlling dimension: inches
- (6) Thermal pad contour optional within dimensions E, H1, D2 and E1
- (7) Dimension E2 x H1 define a zone where stamping and singulation irregularities are allowed
- (8) Outline conforms to JEDEC TO-220, D2 (minimum) where dimensions are derived from the actual package outline



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Revision: 02-Oct-12 Document Number: 91000

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